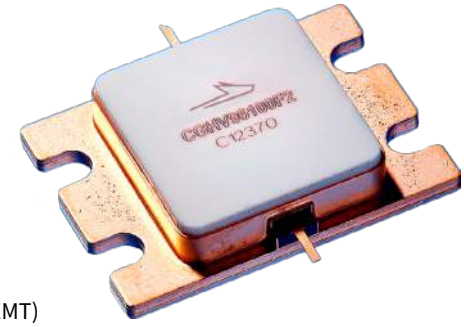
CGHV96100F2

100 W, 8.4 - 9.6 GHz, 50-ohm, Input/Output Matched GaN HEMT



PN: CGHV96100F2
Package Type: 440217

Description

Wolfspeed's CGHV96100F2 is a gallium nitride (GaN) High Electron Mobility Transistor (HEMT) on Silicon Carbide (SiC) substrates. This GaN Internally Matched (IM) FET offers excellent power added efficiency in comparison to other technologies. GaN has superior properties compared to silicon or gallium arsenide, including higher breakdown voltage, higher saturated electron drift velocity and higher thermal conductivity. GaN HEMTs also offer greater power density and wider bandwidths compared to GaAs transistors. This IM FET is available in a metal/ceramic flanged package for optimal electrical and thermal performance.

Typical Performance Over 8.4 - 9.6 GHz (T_C = 25°C)

Parameter	8.4 GHz	8.8 GHz	9.0 GHz	9.2 GHz	9.4 GHz	9.6 GHz	Units
Linear Gain	13.8	12.8	13.0	12.4	11.8	11.4	dB
Output Power	171	163	160	150	137	131	W
Power Gain	10.3	10.1	10.0	9.7	9.4	9.1	dB
Power Added Efficiency	45.5	42.8	41.5	39.2	35.5	35.4	%

Note: Measured in CGHV96100F2-TB (838179) under 100µs pulse width, 10% duty, P_{IN} 42.0 dBm (16 W)

Features

- 8.4 - 9.6 GHz Operation
- 145 W P_{OUT} typical
- 10 dB Power Gain
- 40% Typical PAE
- 50 Ohm Internally Matched
- <0.3 dB Power Droop

Applications

- Marine Radar
- Weather Monitoring
- Air Traffic Control
- Maritime Vessel Traffic Control
- Port Security

Large Signal Models Available for ADS and MWO

RoHS compliant

4600 Silicon Drive | Durham, NC 27703 | Tel: +1.919.313.5300

Absolute Maximum Ratings (not simultaneous)

Parameter	Symbol	Rating	Units	Conditions
Drain-source Voltage	V_{DSS}	120	V	25°C
Gate-source Voltage	V_{GS}	-10, +2		
Power Dissipation	P_{DISS}	222.0	W	Pulsed
Storage Temperature	T_{STG}	-65, +150	°C	
Operating Junction Temperature	T_J	225		
Maximum Drain Current[1]	I_{DMAX}	12	A	
Maximum Forward Gate Current	I_{GMAX}	28.8	mA	25°C
Soldering Temperature[2]	T_S	245	°C	
Screw Torque	τ	40	in-oz	
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.73	°C/W	Pulse Width = 100µs, Duty Cycle = 10%, 85°C, P_{DISS} = 173 W
Case Operating Temperature[3]	T_C	-40, +125	°C	

Notes:
[1] Current limit for long term, reliable operation
[2] Refer to the Application Note on soldering at wolfspeed.com/rf/document-library
[3] See also, the Power Dissipation De-rating Curve on Page 9

Electrical Characteristics (Frequency = 9.6 GHz unless otherwise stated; T_C = 25°C)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics[1]						
Gate Threshold	$V_{GS(th)}$	-3.8	-3.0	-2.3	V	V_{DS} = 10 V, I_D = 28.8 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	–	-2.7	–		V_{DS} = 40 V, I_D = 1000 mA
Saturated Drain Current[2]	I_{DS}	20.7	28.8	–	A	V_{DS} = 6.0 V, V_{GS} = 2.0 V
Drain-Source Breakdown Voltage	V_{BR}	100	–	–	V	V_{GS} = -8 V, I_D = 28.8 mA
RF Characteristics[3]						
Small Signal Gain	S21	10.5	12.4	–	dB	V_{DD} = 40 V, I_{DQ} = 1000 mA, P_{IN} = -20 dBm
Input Return Loss at 8.4 - 9.4 GHz	S11	–	–5.2	-2.8		
Input Return Loss at 9.4 - 9.6 GHz		–	–	-3.3		
Output Return Loss	S22	–	-12.3	-6.0		
Power Output[3,4]	P_{OUT}	100	131.0	–	W	V_{DD} = 40 V, I_{DQ} = 1000 mA, P_{IN} = 41.75 dBm
Power Added Efficiency[3,4]	PAE	30	45	–	%	
Power Gain[3,4]	G_P	–	10.2	–	dB	
Output Mismatch Stress	VSWR	–	–	5:1	Ψ	No damage at all phase angles, V_{DD} = 40 V, I_{DQ} = 1000 mA

Notes:
[1] Measured on wafer prior to packaging
[2] Scaled from PCM data
[3] Measured in CGHV96100F2-AMP (838179) under 100µs pulse width, 10% duty
[4] Fixture loss de-embedded using the following offsets: f = 9.6 GHz. Input = 0.5 dB and Output = 0.5 dBa

CGHV96100F2 Typical Performance

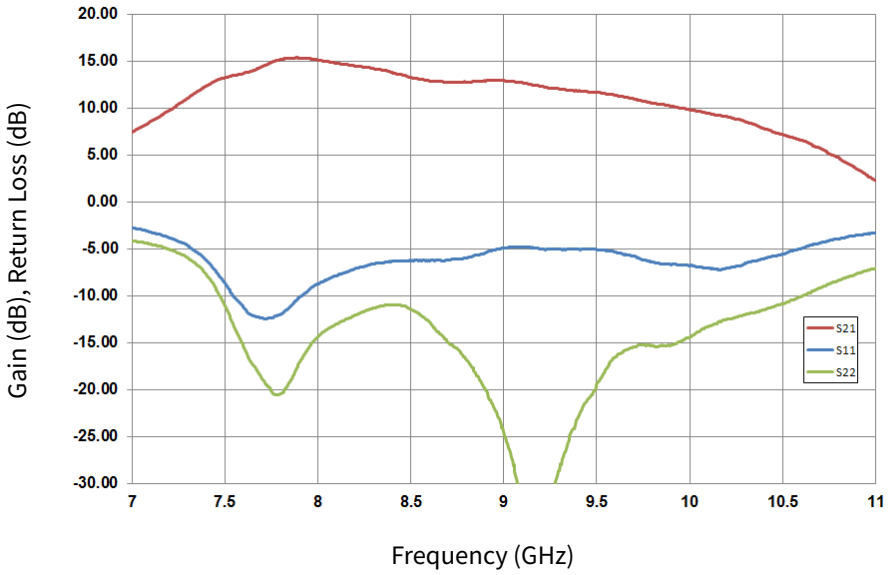


Figure 1. Small Signal Gain and Return Loss vs Frequency of CGHV96100F2 measured in CGHV96100F2-AMP
V_{DS} = 40 V, I_{DQ} = 1000 mA

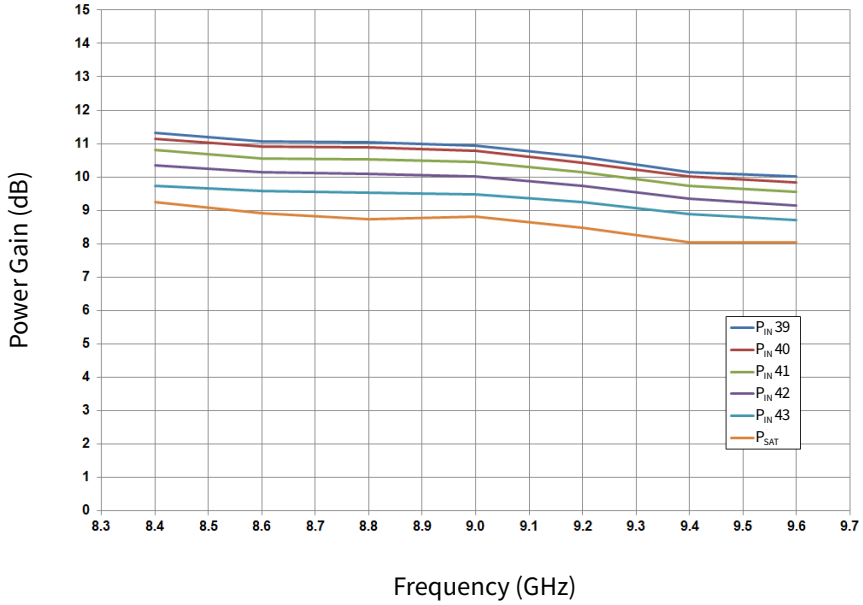


Figure 2. Power Gain vs Frequency and Input Power
V_{DD} = 40 V, Pulse Width = 100µsec, Duty Cycle = 10%

CGHV96100F2 Typical Performance

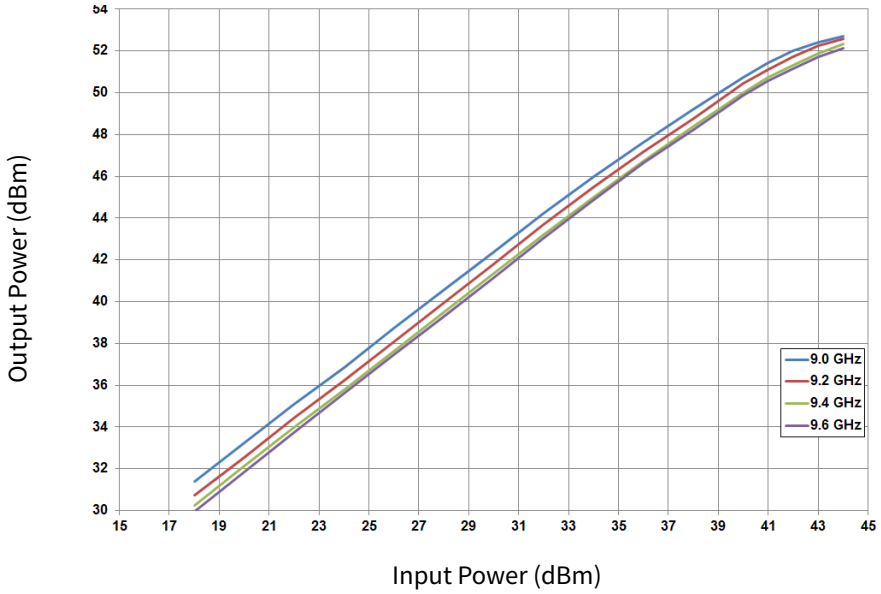


Figure 3. Output Power vs Input Power
V_{DD} = 40 V, Pulse Width = 100µsec, Duty Cycle = 10%

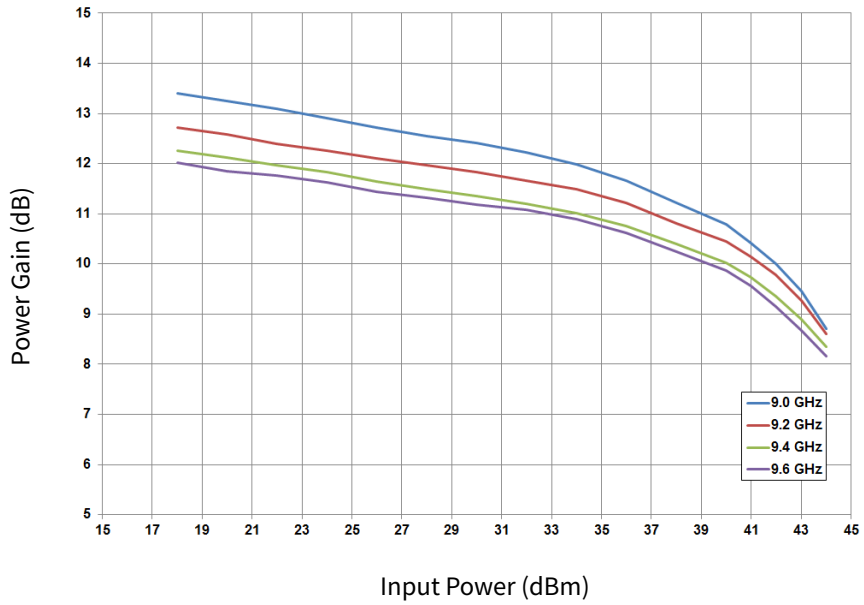


Figure 4. Power Gain vs Frequency and Input Power
V_{DD} = 40 V, Pulse Width = 100µsec, Duty Cycle = 10%

CGHV96100F2 Typical Performance

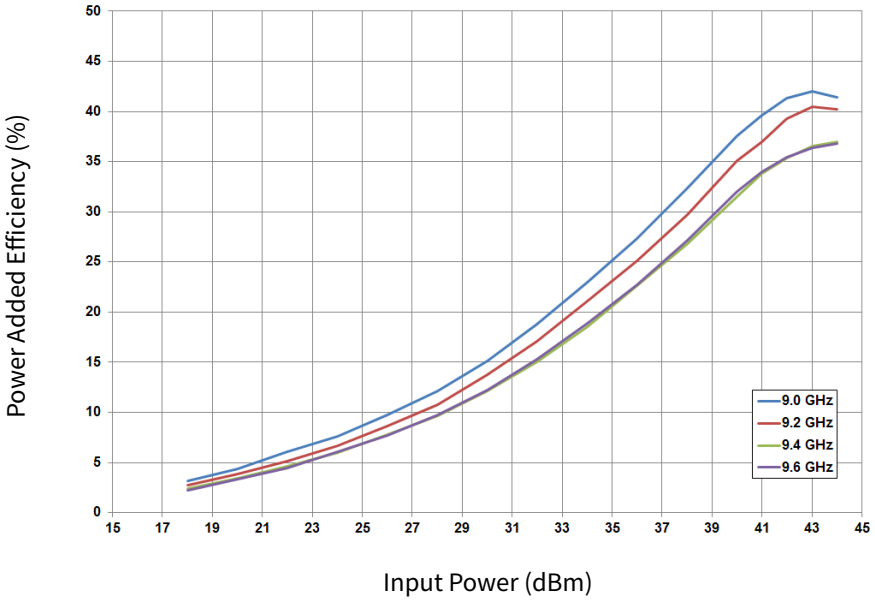


Figure 5. Power Added Efficiency vs Input Power
V_{DD} = 40 V, Pulse Width = 100µsec, Duty Cycle = 10%

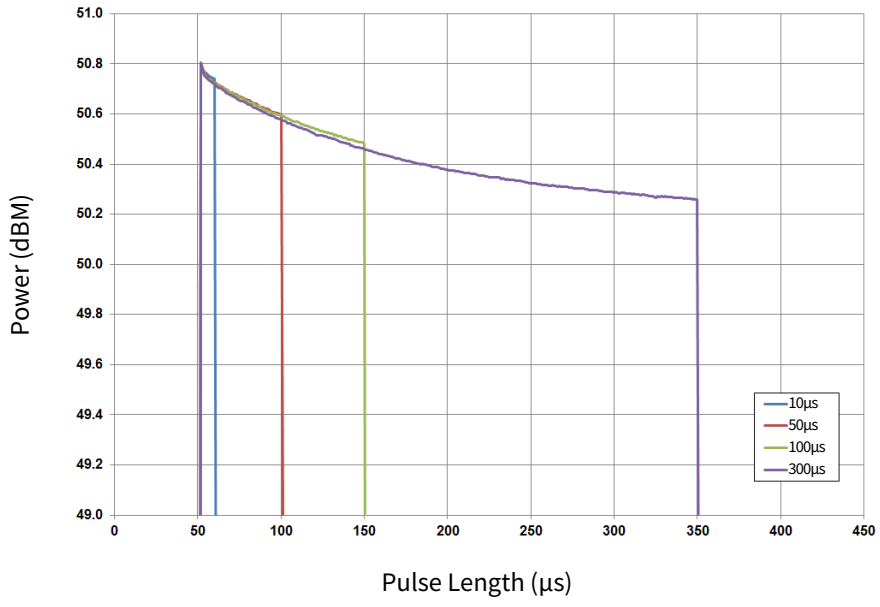


Figure 6. Output Power vs Time
V_{DD} = 40 V, P_{IN} = 41 dBm, Duty Cycle = 10%

CGHV96100F2 Typical Performance

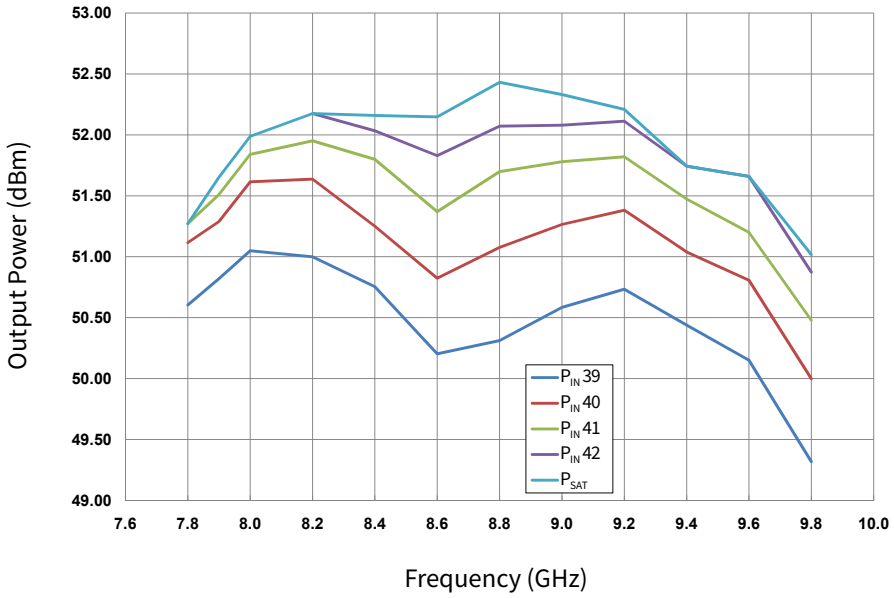


Figure 7. Output Power vs Input Power & Frequency
V_{DD} = 40 V, Pulse Width = 100µsec, Duty Cycle = 10%

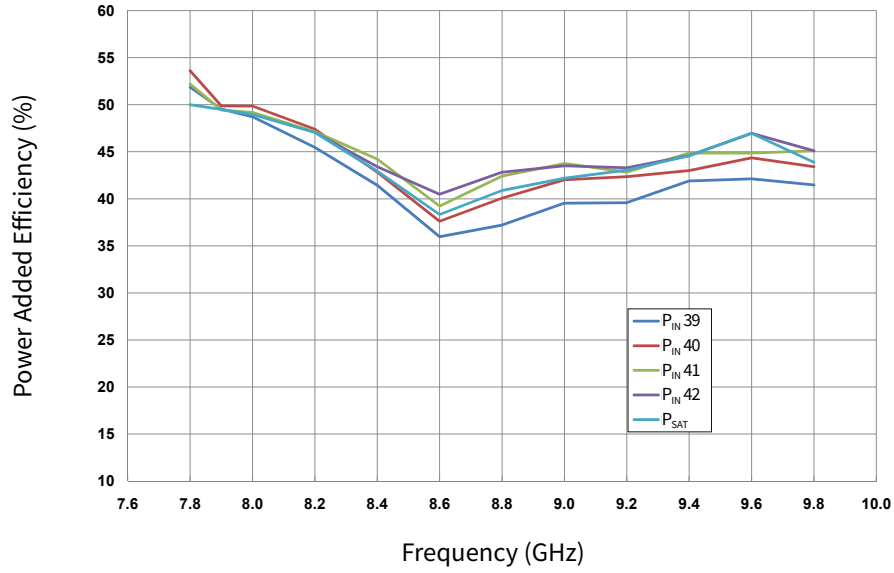
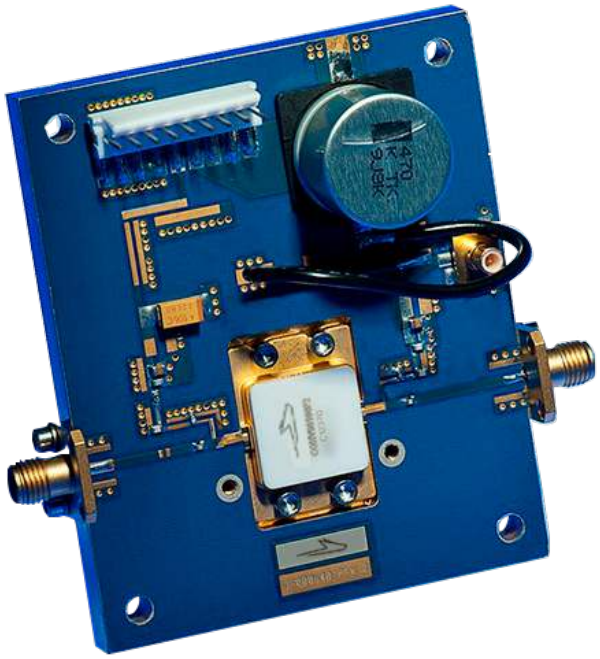


Figure 8. Power Added Efficiency vs Input Power & Frequency
V_{DD} = 40 V, Pulse Width = 100µsec, Duty Cycle = 10%

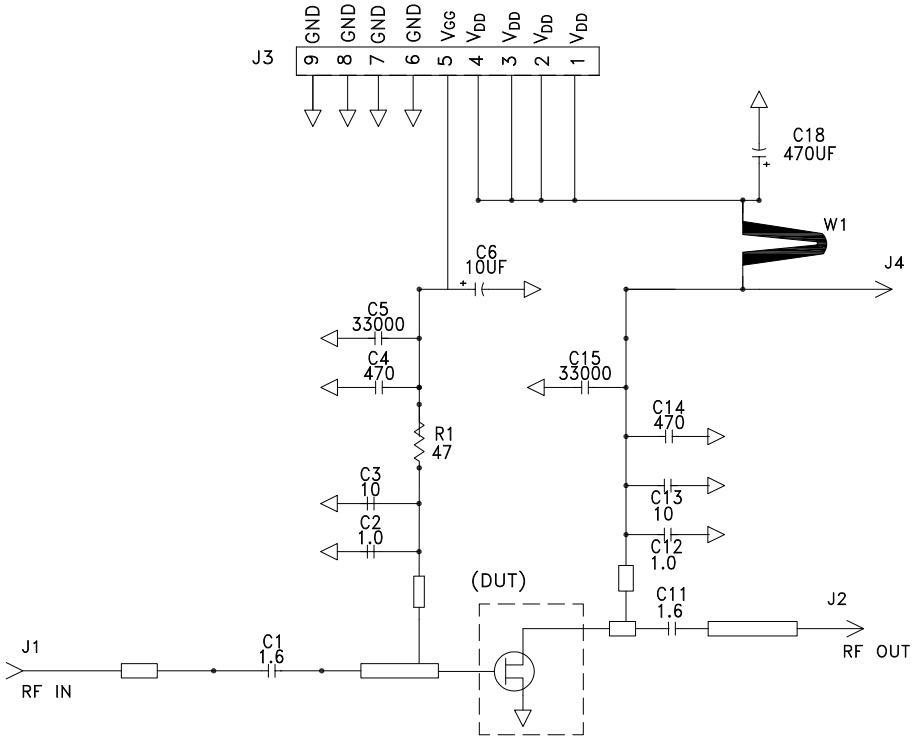
CGHV96100F2-AMP Demonstration Amplifier Circuit Bill of Materials

Designator	Description	Qty
R1	RES, 47 OHM +/-1%, 1/16 W, 0603, SMD	1
C1, C11	CAP, 1.6pF, +/- 0.1pF, 200V, 0402, ATC 600L	2
C2, C12	CAP, 1.0pF, +/- 0.1pF, 200V, 0402 ATC 600L	2
C3, C13	CAP, 10pF +/-5%, 0603, ATC	2
C4, C14	CAP, 470pF +/-5%, 100 V, 0603	2
C5, C15	CAP, 33000pF, 0805, 100 V, X7R	2
C6	CAP, 10µF, 16 V, TANTALUM	1
C18	CAP, 470µF +/-20%, ELECTROLYTIC	1
J1, J2	CONNECTOR, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST, 20MIL	2
J3	CONNECTOR, HEADER, RT>PLZ .1CEN LK 9POS	1
J4	CONNECTOR, SMB, STRAIGHT JACK	1
-	PCB, TEST FIXTURE, TACONICS RF35P, 20 MIL THK, 440210 PKG	1
-	2-56 SOC HD SCREW 1/4 SS	4
-	#2 SPLIT LOCKWASHER SS	4
Q1	CGHV96100F2	1

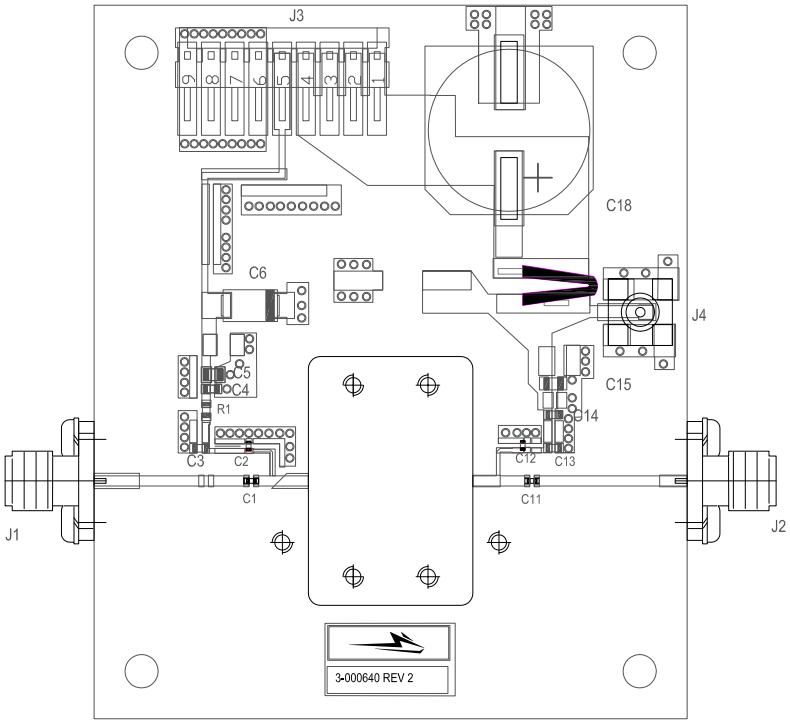
CGHV96100F2-AMP Demonstration Amplifier Circuit



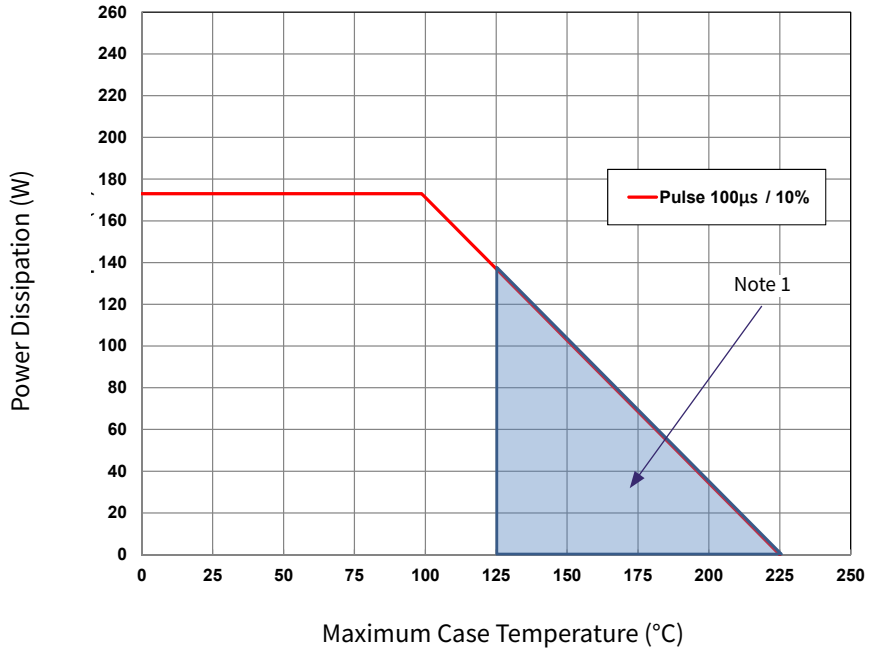
CGHV96100F2-AMP Demonstration Amplifier Circuit Schematic



CGHV96100F2-AMP Demonstration Amplifier Circuit Outline

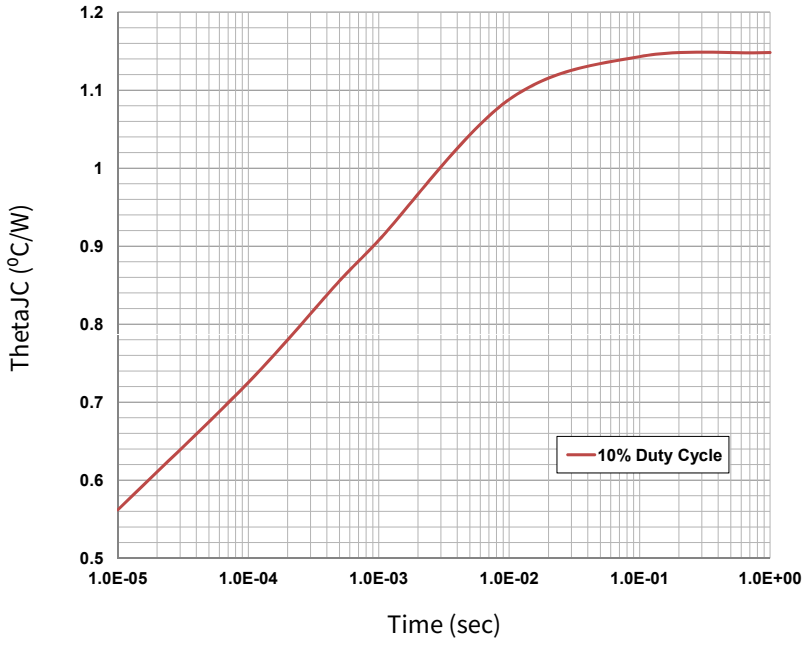


CGHV96100F2 Power Dissipation De-rating Curve



Note. Shaded area exceeds Maximum Case Operating Temperature (See Page 2)

CGHV96100F2 Transient Curve

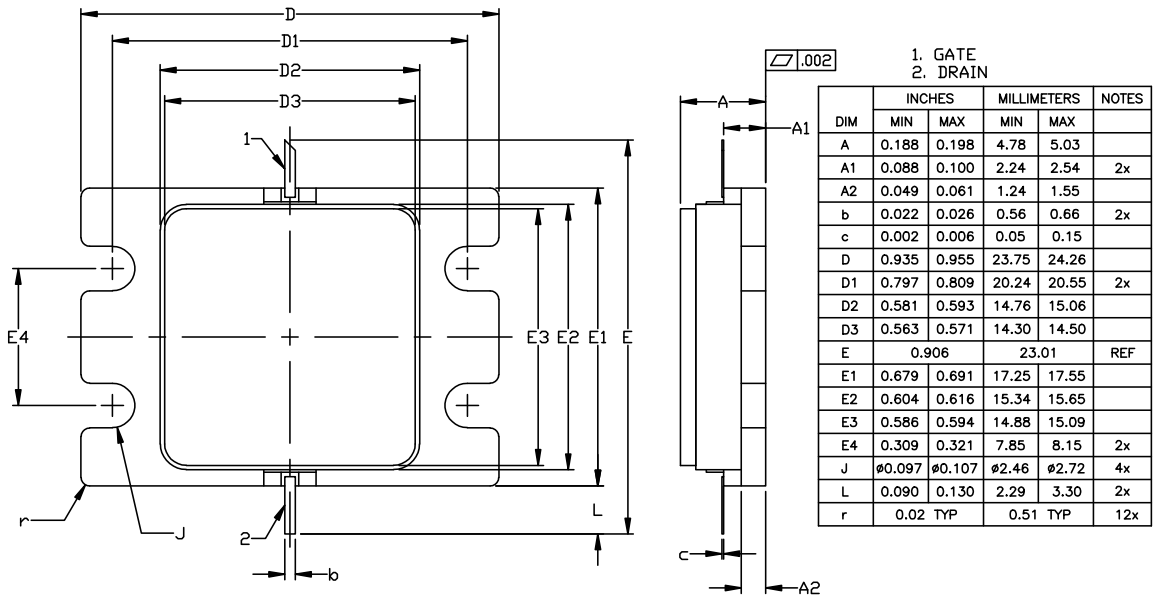


Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Classification Level	Test Methodology
Human Body Model	HBM	2	ANSI/ESDA/JEDEC JS-001 Table 3	JEDEC JESD22 A114-D
Charge Device Model	CDM	C3	ANSI/ESDA/JEDEC JS-002 Table 3	JEDEC JESD22 C101-C

Product Dimensions CGHV96100F2 (Package Type — 440217)

NOTES: (UNLESS OTHERWISE SPECIFIED)
1. INTERPRET DRAWING IN ACCORDANCE WITH ANSI Y14.5M-2009
2. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF .020 BEYOND EDGE OF LID
3. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF .008 IN ANY DIRECTION
4. ALL PLATED SURFACES ARE GOLD OVER NICKEL



DIM	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.188	0.198	4.78	5.03	
A1	0.088	0.100	2.24	2.54	2x
A2	0.049	0.061	1.24	1.55	
b	0.022	0.026	0.56	0.66	2x
c	0.002	0.006	0.05	0.15	
D	0.935	0.955	23.75	24.26	
D1	0.797	0.809	20.24	20.55	2x
D2	0.581	0.593	14.76	15.06	
D3	0.563	0.571	14.30	14.50	
E	0.906		23.01		REF
E1	0.679	0.691	17.25	17.55	
E2	0.604	0.616	15.34	15.65	
E3	0.586	0.594	14.88	15.09	
E4	0.309	0.321	7.85	8.15	2x
J	ø0.097	ø0.107	ø2.46	ø2.72	4x
L	0.090	0.130	2.29	3.30	2x
r	0.02 TYP		0.51 TYP		12x

Part Number System

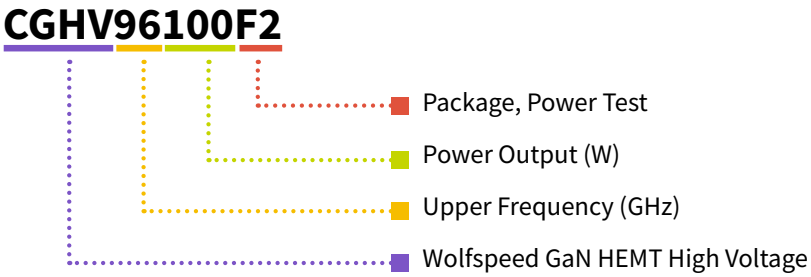


Table 1.

Parameter	Value	Units
Upper Frequency[1]	9.6	GHz
Power Output	100	W
Package	Flange	–

Note:
[1] Alpha characters used in frequency code indicate a value greater than 9.9 GHz. See Table 2 for value.

Table 2.

Character Code	Code Value
A	0
B	1
C	2
D	3
E	4
F	5
G	6
H	7
J	8
K	9
Examples	1A = 10.0 GHz 2H = 27.0 GHz

Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGHV96100F2	GaN HEMT	Each	
CGHV96100F2-AMP	Test board with GaN HEMT	Each	

For more information, please contact:

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Tel: +1.919.313.5300
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RF Product Marketing Contact
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Notes & Disclaimer

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